Silicon NPN Power Transistors 2SC1050

DESCRIPTION
·With TO-3 package
·High breakdown voltage

APPLICATIONS
·For use in audio and general purpose applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

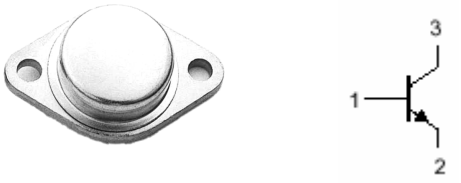


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		1	A
P_T	Total power dissipation	T_{mb}=25?	40	W
T_j	Junction temperature		150	?
T_{stg}	Storage temperature		-55~150	?

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CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1A ; I_B=0	300			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=0.5A; I_B=0.1A			1.2	V
V_{BEsat}	Base-emitter saturation voltage	I_C=0.5A; I_B=0.1A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=300V; I_E=0			0.1	mA
I_{CEO}	Collector cut-off current	V_{CE}=300V; I_B=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=0.3A ; V_{CE}=5V	30		200	

PACKAGE OUTLINE

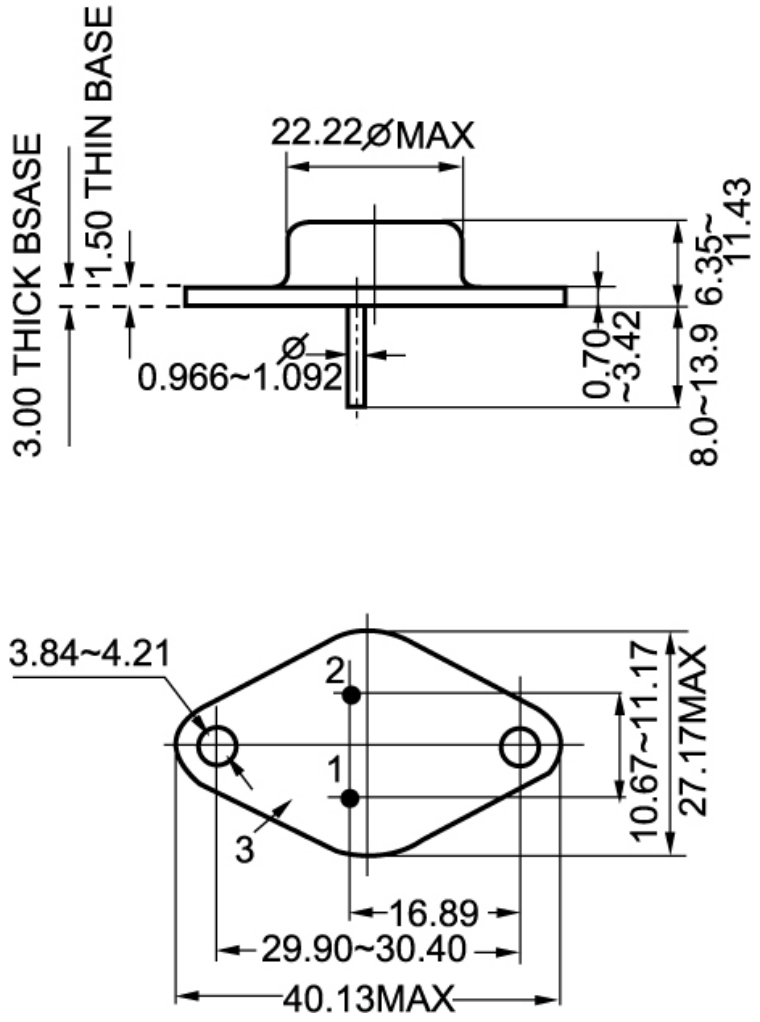


Fig.2 Outline dimensions